

ABSTRACT
PROCESS FOR FABRICATING A STRUCTURE HAVING A BURIED
DIELECTRIC LAYER OF UNIFORM THICKNESS

5 The invention relates to a process for fabricating a final
structure (5) comprising in succession a useful
semiconductor layer (3'), a dielectric layer (2) and a
carrier substrate (4), the process comprising a step of
10 providing an intermediate structure (1) including an upper
layer (3), the dielectric layer (2) and the carrier
substrate (4) and a step of finishing the intermediate
structure (1) to form the final structure (5) comprising a
treatment modifying nonuniformly the thickness of the
15 dielectric layer (2) following a determined dissolution
profile. According to the invention, the dielectric layer
(2) of the intermediate structure (1) has a thickness
profile complementary to the determined dissolution
profile.

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Figure 2b